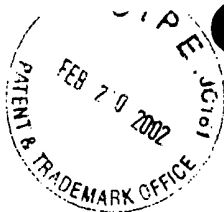


ASMEX.186DV1



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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Raaijmakers et al. ) Group Art Unit 2812  
App. No. : 09/764,711 )  
Filed : January 18, 2001 )  
For : METHOD OF DEPOSITING )  
SILICON WITH HIGH STEP )  
COVERAGE )  
Examiner : Roman, A. )

#5/IDS  
3/7/02  
V. Vannell

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

Enclosed is form PTO-1449 listing 5 references that are also enclosed. This Information Disclosure Statement is being filed under 37 C.F.R. § 1.97(c)(2) before the mailing date of a final action and before the mailing of a Notice of Allowance. This Statement is accompanied by the fees set forth in 37 C.F.R. § 1.17(p). The Commissioner is hereby authorized to charge any additional fees which may be required or to credit any overpayment to Account No. 11-1410.

02/26/2002 ASMEX.186DV1 012402 11-1410

01 01/18/02

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: January 24, 2002

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ASMEX.186DV1COPY OF PAPERS  
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09/764,711APPLICANT  
Raaijmakers et al.FILING DATE  
January 18, 2001GROUP  
2812INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO

## OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

EXAMINER INITIAL	
	Coffa et al., "Defect Production and Annealing in Ion-Implanted Amorphous Silicon," Physical Review Letters, Vol. 70, No. 24, (June 14, 1993), pp.3756-3759.
	Kakkad et al., "Crystallized Si films by low-temperature rapid thermal annealing of amorphous silicon," J. Appl. Phys., Vol. 65, No. 5, (March 1, 1989), pp. 2069-2072.
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EXAMINER

DATE CONSIDERED

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.